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(54) Title: COMPONENT, SYSTEM, AND METHOD FOR IMPROVED FORELINE CLEANING

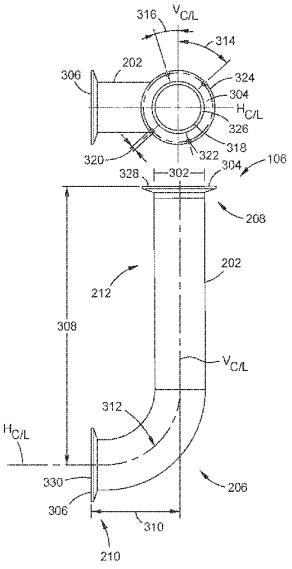

FIG. 3

(57) Abstract: A component, system, and method for improved foreline cleaning of semiconductor chambers and components are disclosed herein. In one example, a processing chamber component includes a foreline constructed from stainless steel having a circular cross sectional shape and an inner surface. The foreline further includes a first end configured to couple to a processing chamber, a second end configured to couple to a valve, and a coating disposed within the inner surface of the foreline, the coating having a thickness between about 150 nanometers and about 525 nanometer. Further, the first end includes a first flange, the second end comprises a second flange, wherein the first end and the second end are coupled by a bend. Further, the coating has properties configured to reduce depositions within the foreline.

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